

# MOSFET – SiC Power, Single N-Channel, D2PAK-7L

## 1200 V, 80 mΩ, 30 A



ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

## NVBG080N120SC1

### Features

- Typ.  $R_{DS(on)} = 80 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_{G(tot)} = 56 \text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss} = 79 \text{ pF}$ )
- 100% Avalanche Tested
- Qualified According to AEC-Q101
- This Device is Pb-Free and is RoHS Compliant

### Typical Applications

- Automotive On Board Charger
- Automotive DC/DC Converter for EV/HEV

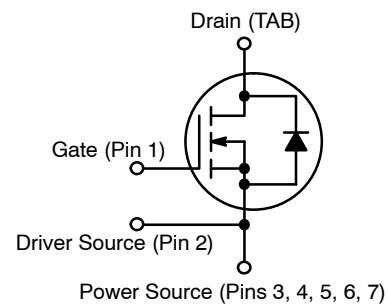
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	1200	V	
Gate-to-Source Voltage		$V_{GS}$	-15/+25	V	
Recommended Operation Values of Gate - Source Voltage		$T_C < 175^\circ\text{C}$ $V_{GSop}$	-5/+20	V	
Continuous Drain Current (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	30	A
			$P_D$	179	W
Continuous Drain Current (Note 1)	Steady State	$T_C = 100^\circ\text{C}$	$I_D$	21	A
			$P_D$	89	W
Pulsed Drain Current (Note 2)		$T_C = 25^\circ\text{C}$	$I_{DM}$	132	A
Single Pulse Surge Drain Current Capability	$T_C = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$ , $R_G = 4.7 \Omega$		$I_{DSC}$	132	A
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	18	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_L = 23 \text{ A}_{pk}$ , $L = 1 \text{ mH}$ ) (Note 3)		$E_{AS}$	265	mJ	
Maximum Lead Temperature for Soldering, 1/8" from Case for 10 Seconds		$T_L$	300	$^\circ\text{C}$	

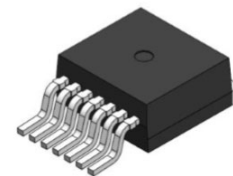
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3.  $E_{AS}$  of 265 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1 \text{ mH}$ ,  $I_{AS} = 23 \text{ A}$ ,  $V_{DD} = 120 \text{ V}$ ,  $V_{GS} = 18 \text{ V}$ .

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
1200 V	110 mΩ @ 20 V	30 A

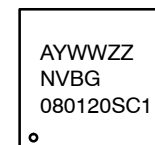


N-CHANNEL MOSFET



D2PAK-7L  
CASE 418BJ

### MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Lot Traceability
- NVBG080120SC1 = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

# NVBG080N120SC1

**Table 1. THERMAL CHARACTERISTICS**

Parameter	Symbol	Max	Units
Thermal Resistance Junction-to-Case (Note 1)	$R_{\theta JC}$	0.84	°C/W
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	°C/W

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1\text{ mA}$ , refer to $25^\circ\text{C}$		0.5		V/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$ $V_{DS} = 1200\text{ V}$	$T_J = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_J = 175^\circ\text{C}$		1	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +25/-15\text{ V}, V_{DS} = 0\text{ V}$			$\pm 1$	$\mu\text{A}$

**ON CHARACTERISTICS** (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 5\text{ mA}$	1.8	3	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5		+20	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 25^\circ\text{C}$		80	110	m $\Omega$
		$V_{GS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 150^\circ\text{C}$		121	175	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 20\text{ V}, I_D = 20\text{ A}$		11		S

**CHARGES, CAPACITANCES & GATE RESISTANCE**

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz},$ $V_{DS} = 800\text{ V}$		1154		pF
Output Capacitance	$C_{OSS}$			79		
Reverse Transfer Capacitance	$C_{RSS}$			7.9		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/20\text{ V}, V_{DS} = 600\text{ V},$ $I_D = 20\text{ A}$		56		nC
Threshold Gate Charge	$Q_{G(TH)}$			10		
Gate-to-Source Charge	$Q_{GS}$			18		
Gate-to-Drain Charge	$Q_{GD}$			11		
Gate-Resistance	$R_G$	$f = 1\text{ MHz}$		1.2		$\Omega$

**SWITCHING CHARACTERISTICS** (Note )

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/20\text{ V}, V_{DS} = 800\text{ V},$ $I_D = 20\text{ A}, R_G = 4.7\ \Omega,$ Inductive Load		12	22	ns
Rise Time	$t_r$			12	22	
Turn-Off Delay Time	$t_{d(OFF)}$			21	34	
Fall Time	$t_f$			9	18	
Turn-On Switching Loss	$E_{ON}$			135		$\mu\text{J}$
Turn-Off Switching Loss	$E_{OFF}$			46		
Total Switching Loss	$E_{TOT}$			181		

**DRAIN-SOURCE DIODE CHARACTERISTICS**

Continuous Drain-Source Diode Forward Current	$I_{SD}$	$V_{GS} = -5\text{ V}, T_J = 25^\circ\text{C}$			18	A
Pulsed Drain-Source Diode Forward Current (Note 2)	$I_{SDM}$	$V_{GS} = -5\text{ V}, T_J = 25^\circ\text{C}$			132	A
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5\text{ V}, I_{SD} = 10\text{ A}, T_J = 25^\circ\text{C}$		3.9		V

# NVBG080N120SC1

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Reverse Recovery Time	$t_{RR}$	$V_{GS} = -5/20\text{ V}$ , $I_{SD} = 20\text{ A}$ , $di_S/dt = 1000\text{ A}/\mu\text{s}$		16.2		ns
Reverse Recovery Charge	$Q_{RR}$			61.6		nC
Reverse Recovery Energy	$E_{REC}$			4.1		$\mu\text{J}$
Peak Reverse Recovery Current	$I_{RRM}$			7.6		A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Switching characteristics are independent of operating junction temperature

# NVBG080N120SC1

## TYPICAL CHARACTERISTICS

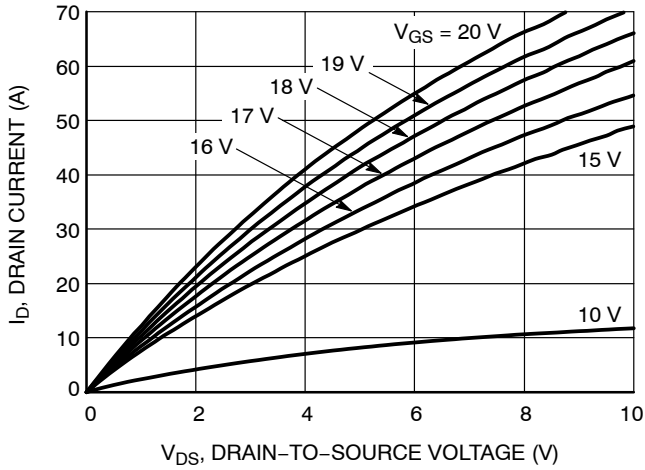


Figure 1. On-Region Characteristics

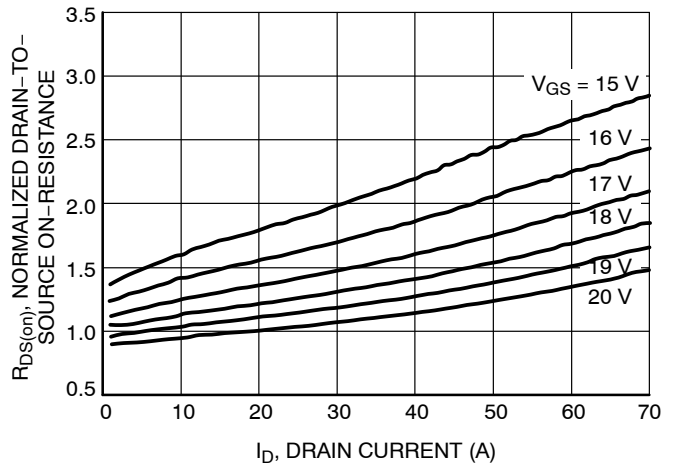


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

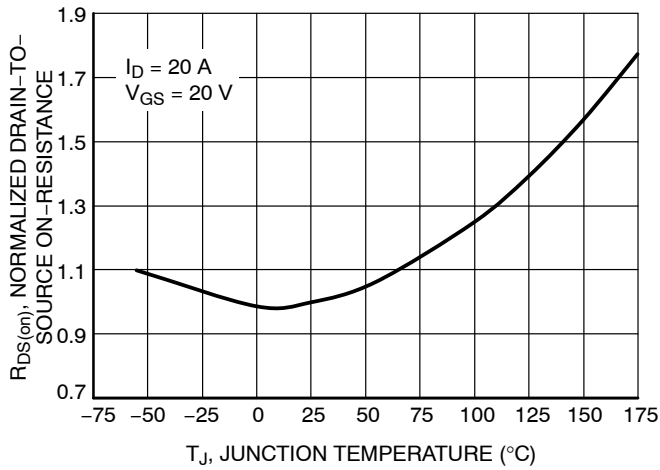


Figure 3. On-Resistance Variation with Temperature

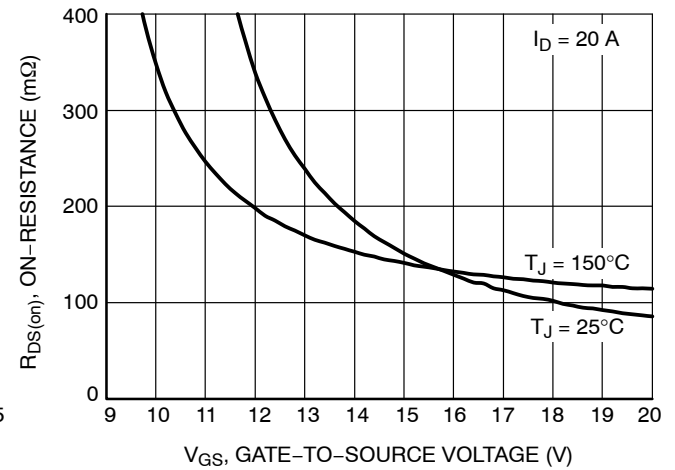


Figure 4. On-Resistance vs. Gate-to-Source Voltage

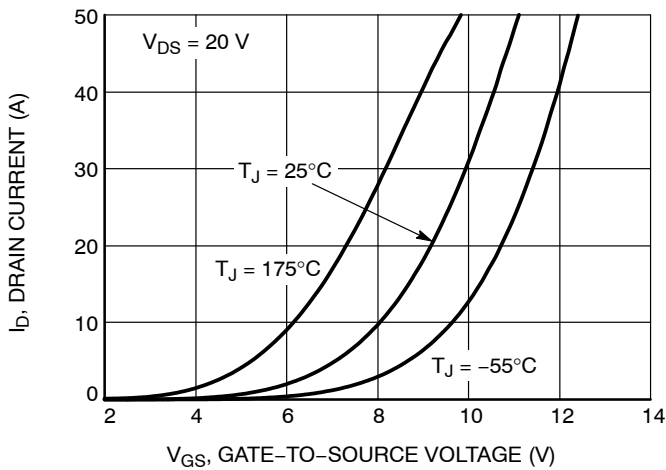


Figure 5. Transfer Characteristics

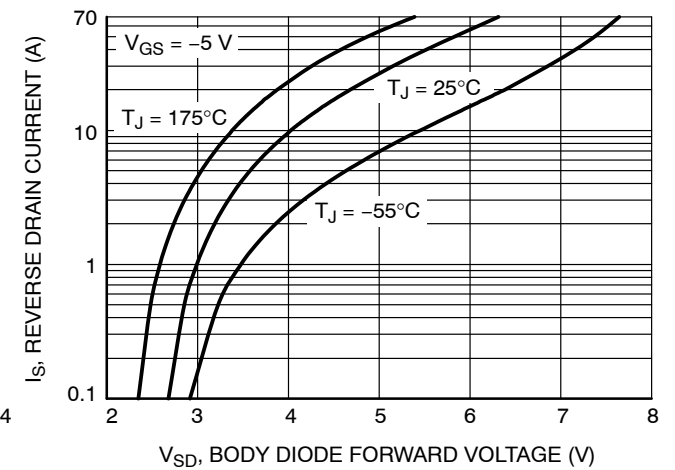
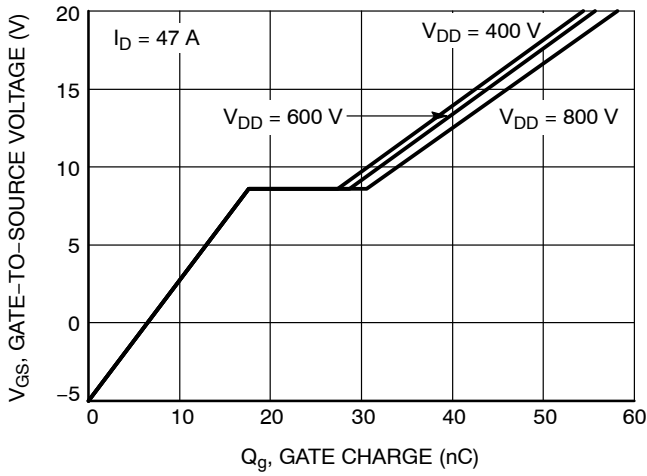


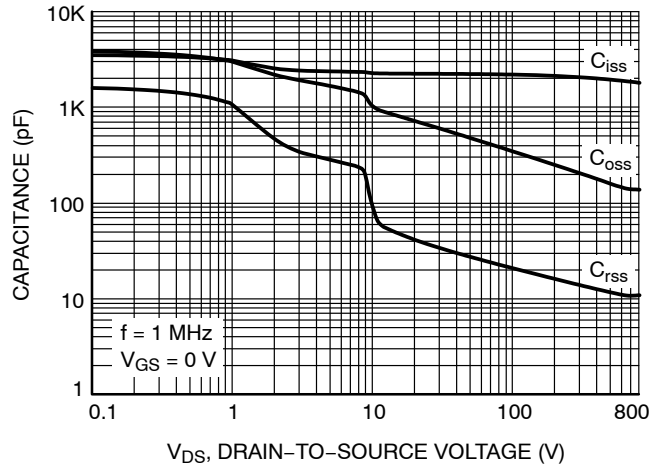
Figure 6. Diode Forward Voltage vs. Current

# NVBG080N120SC1

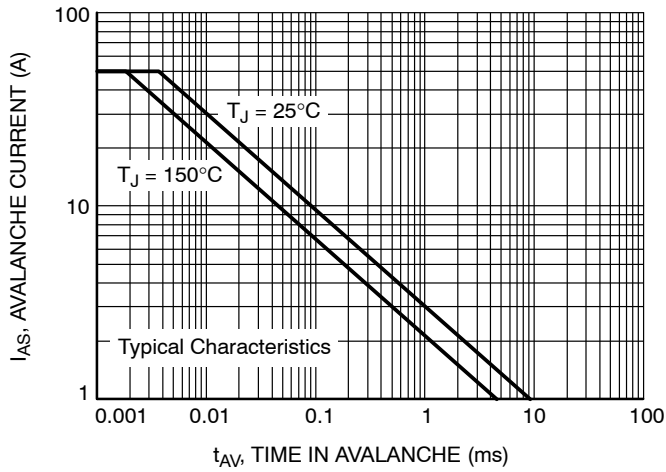
## TYPICAL CHARACTERISTICS



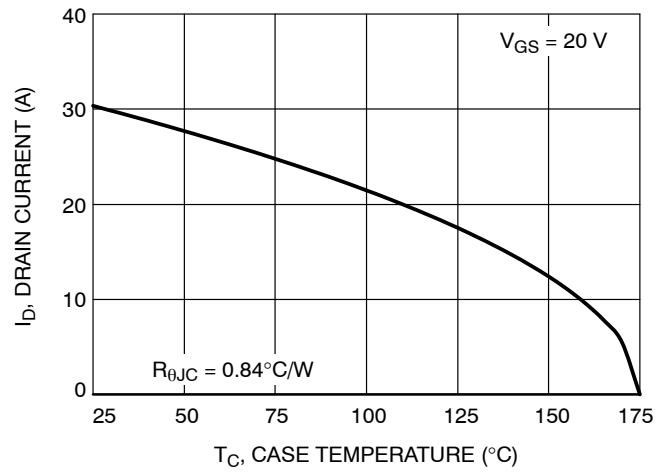
**Figure 7. Gate-to-Source Voltage vs. Total Charge**



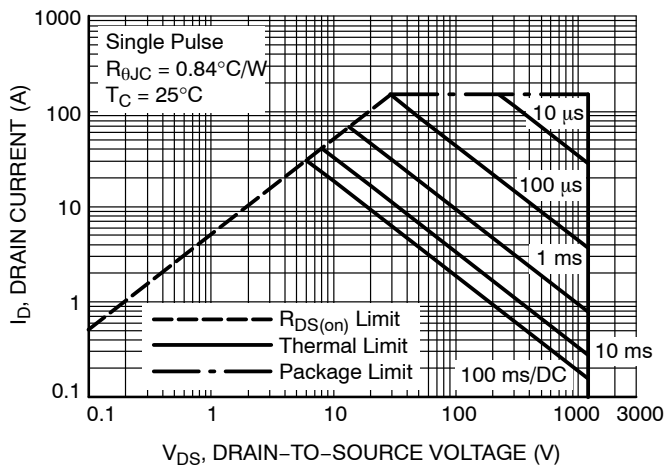
**Figure 8. Capacitance vs. Drain-to-Source Voltage**



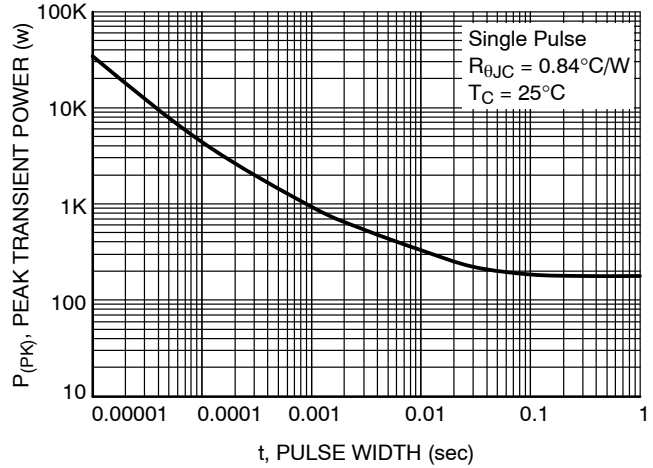
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**



**Figure 11. Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

# NVBG080N120SC1

## TYPICAL CHARACTERISTICS

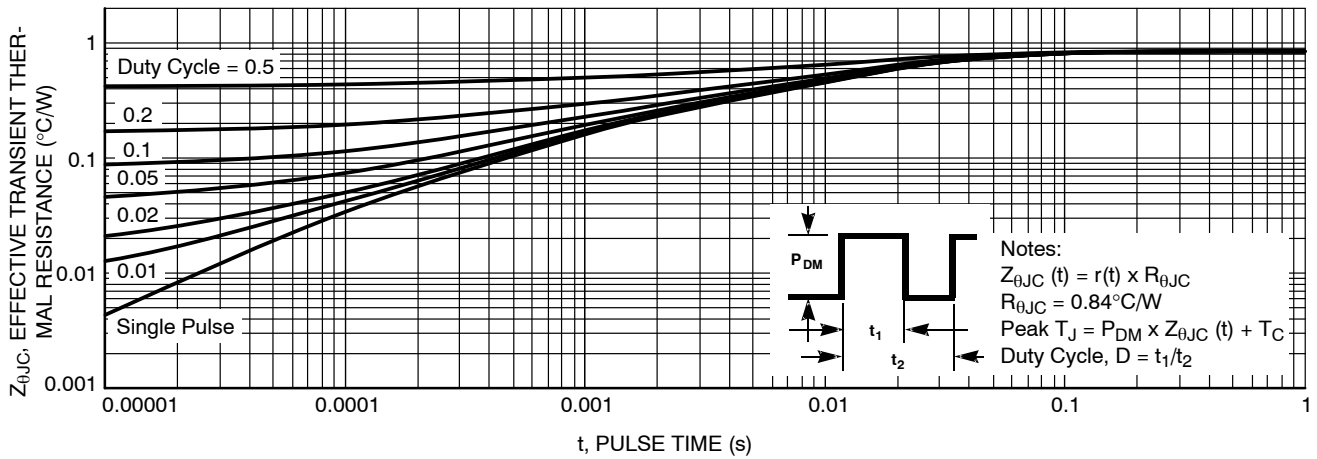


Figure 13. Junction-to-Case Transient Thermal Response Curve

### DEVICE ORDERING INFORMATION

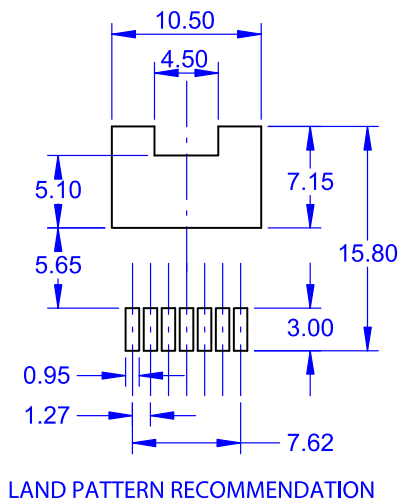
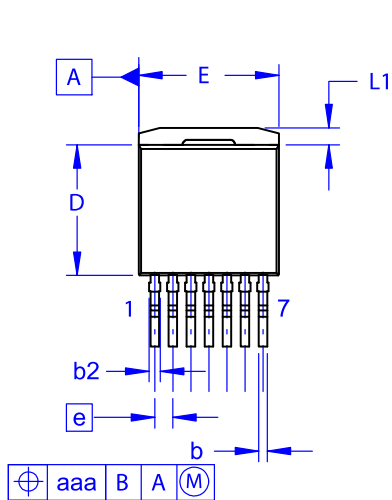
Device	Package	Shipping†
NVBG080N120SC1	D2PAK-7L	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NVBG080N120SC1

## PACKAGE DIMENSIONS

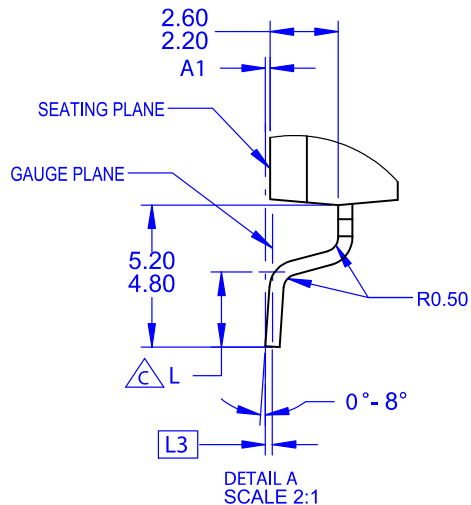
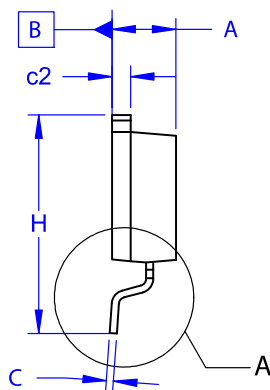
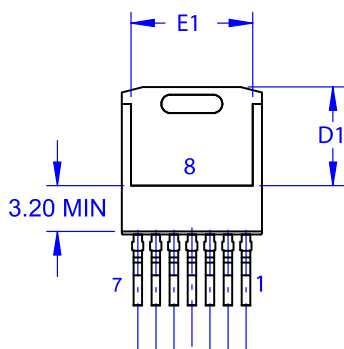
**D<sup>2</sup>PAK7 (TO-263-7L HV)**  
CASE 418BJ  
ISSUE B




**NOTES:**

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. OUT OF JEDEC STANDARD VALUE.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.60	0.70	0.80
b	0.51	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	6.15	6.80	7.15
E	9.70	9.90	10.20
E1	7.15	7.65	8.15
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25



# NVBG080N120SC1

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

North American Technical Support:  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative